

Features

Low forward voltage drop
High reverse voltage
Hermetic metal cases with ceramic insulators

Typical Applications

All purpose high power rectifier diodes
High power resistance welding equipment
Non-controllable and half-controllable rectifiers
Controlled rectifiers

Part No. Y30ZPB-ZT25aT		
$I_{F(AV)}$	**1230A**	
V_{RRM}	**200V**	**400V**
	600V	**800V**
	1000V	**1200V**
	1400V	

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(C)	VALUE			UNIT
					Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180 half sine wave 50Hz Double side cooled,	T_C=85 C	190			1230	A
V_{RRM}	Repetitive peak reverse voltage	tp=10ms		190	200		1400	V
I_{RRM}	Repetitive peak current	at V_{RRM}		190			30	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}		190			11	kA
I^2t	I^2t for fusing coordination						605	A^2s*10^3
V_{FO}	Threshold voltage			190			0.95	V
r_F	Forward slope resistance						0.31	mΩ
V_{FM}	Peak forward voltage	I_{FM}=1200A, F=7.0kN		25			1.80	V
Q_{rr}	Recovery charge	I_{FM}=1000A, tp=4000μs, di/dt=-20A/μs, V_R=100V		190		1600		μC
$R_{th(j-C)}$	Thermal resistance Junction to case	At 180^0 sine double side cooled Clamping force 7.0kN					0.045	C /W
$R_{th(C-h)}$	Thermal resistance case to heat sink						0.010	
F_m	Mounting force				5.3		10	kN
T_{vj}	Junction temperature				-40		190	C
T_{stg}	Stored temperature				-40		190	C
W_t	Weight					80		g
Outline	ZT25aT							

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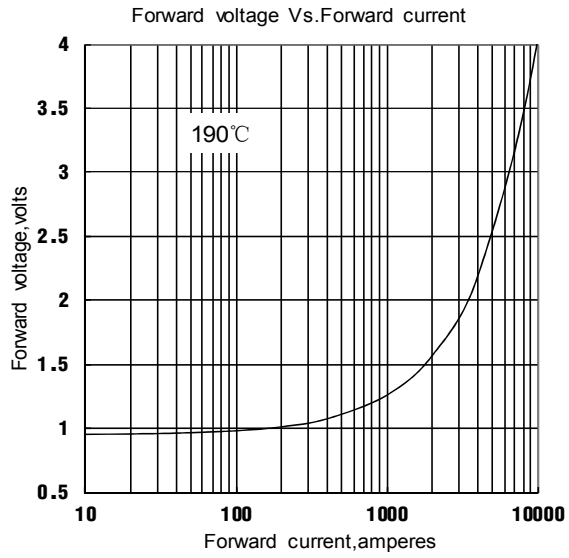


Fig1

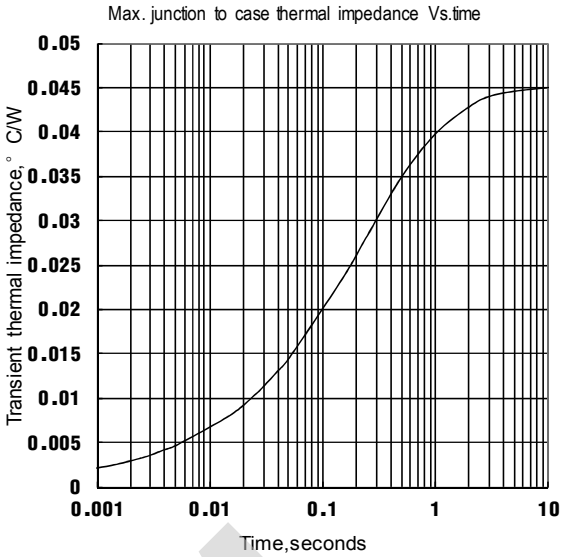


Fig2

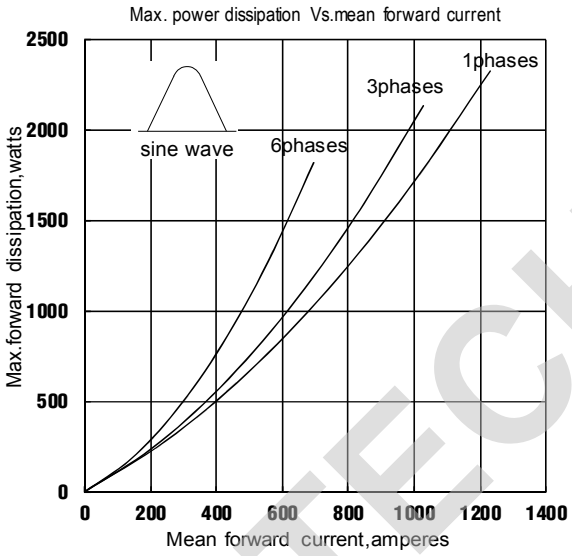


Fig3

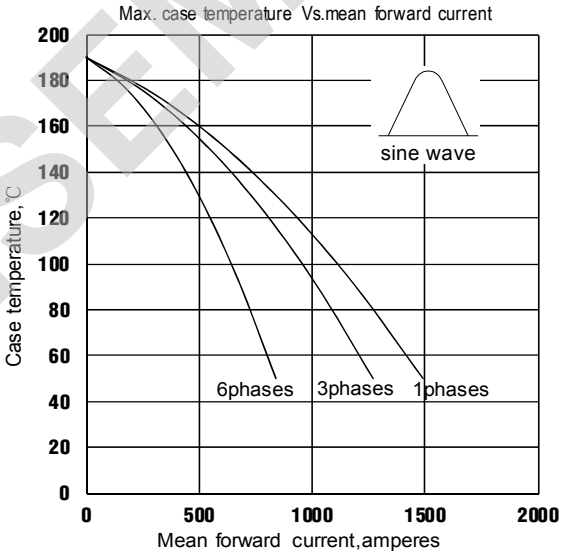


Fig4

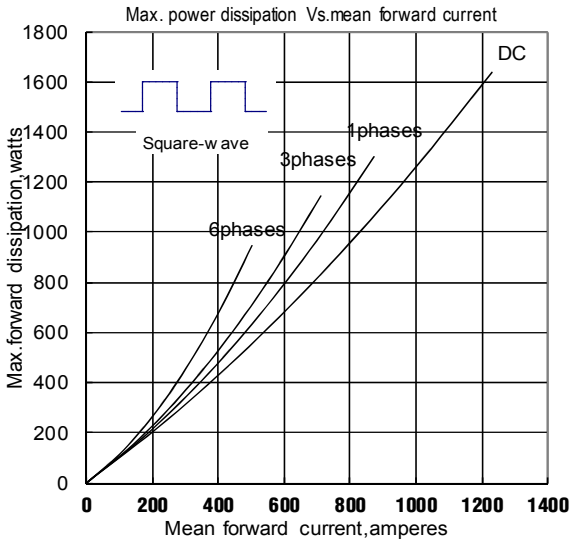


Fig5

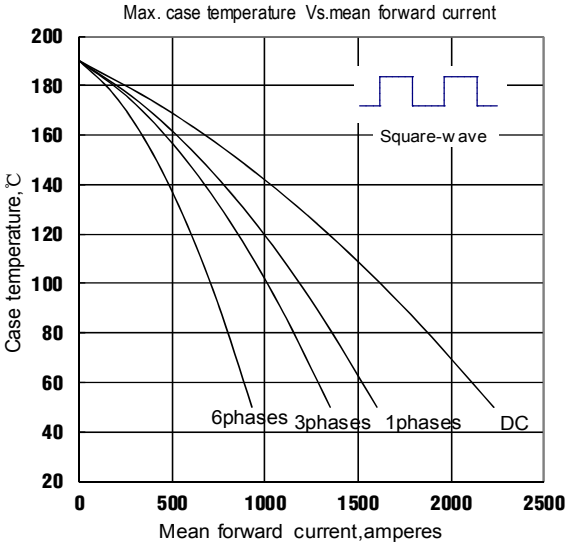


Fig6

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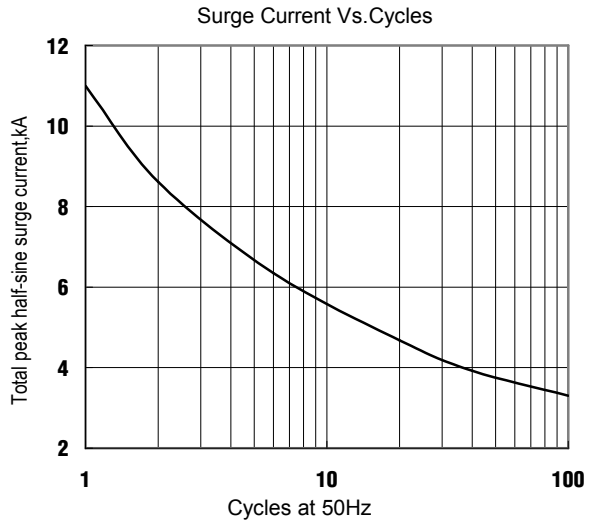


Fig.7

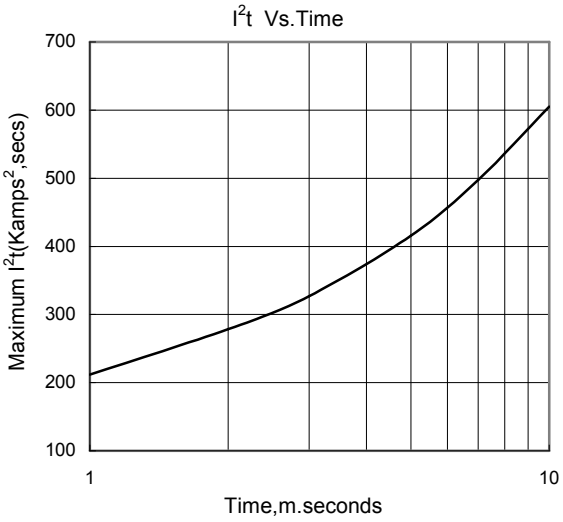
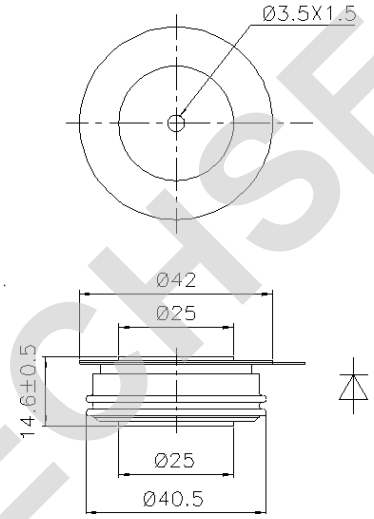


Fig.8

Outline:



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TECHSEM reserves the right to change specifications without notice.